

S/N 10/751,091

PATENT

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

Applicant: Moeckly et al. Examiner: Paul A. Wartalowicz  
Serial No.: 10/751,091 Group Art Unit: 1754  
Filed: 01/02/2004 Docket No.: 10467.0043USI2

O I P E Title:  
1449

HIGH-TEMPERATURE SUPERCONDUCTOR DEVICES AND  
METHODS OF FORMING THE SAME

CERTIFICATE UNDER 37 CFR 1.8:

I hereby certify that this correspondence is being deposited with the United States Postal Service as first class mail, with sufficient postage, in an envelope addressed to: Mail Stop Amendment, Commissioner for Patents, P.O. Box 1450, Alexandria, Virginia 22313-1450 July 5, 2007.

  
By:  
Name: Lisa Hill

SUPPLEMENTAL INFORMATION DISCLOSURE STATEMENT (37 C.F.R. § 1.97(b))

Mail Stop Amendment  
Commissioner for Patents  
P.O. Box 1450  
Alexandria, Virginia 22313-1450

Dear Sir:

With regard to the above-identified application, the items of information listed on the enclosed Form 1449 are brought to the attention of the Examiner.

This statement should be considered because it is submitted before the mailing date of a first Office Action on-the-merits. Accordingly, no fee is due for consideration of the items listed on the enclosed Form 1449.

In accordance with 37 C.F.R. §1.98(d), a copy of each document or other information listed on the enclosed Form 1449 is not provided because it was previously cited by or submitted to the U.S. Patent and Trademark Office in parent application, U.S. Serial No. 10/704,215 filed on November 6, 2003.

No representation is made that a reference is "prior art" within the meaning of 35 U.S.C. §§ 102 and 103 and Applicants reserve the right, pursuant to 37 C.F.R. § 1.131 or otherwise, to establish that the reference(s) are not "prior art." Moreover, Applicants do not represent that a reference has been thoroughly reviewed or that any relevance of any portion of a reference is intended.

Consideration of the items listed is respectfully requested. Pursuant to the provisions of M.P.E.P. 609, it is requested that the Examiner return a copy of the attached Form 1449, marked as being considered and initialed by the Examiner, to the undersigned with the next official communication.

Please charge any additional fees or credit any overpayment to Deposit Account No. 13-2725.



Respectfully submitted,

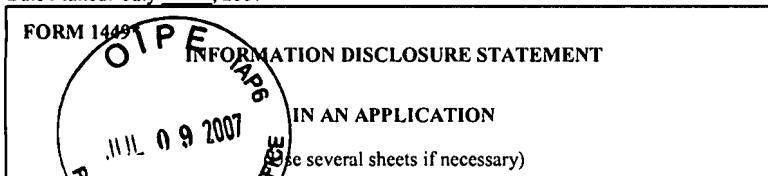
MERCHANT & GOULD  
P. O. Box 2903  
Minneapolis, Minnesota 55402-0903  
(612) 336-4611

Date: July 5, 2007

By Tong Wu  
Tong Wu  
Reg. No. 43,361

Date Mailed: July 5, 2007

Sheet 1 of 3

 <small>JUL 09 2007</small>	Docket Number:	Application Number:
	10467.43USI2	10/751,091
	Applicant: MOECKLY ET AL.	
	Filing Date: 01/02/2004	Group Art Unit: 1754

U.S. PATENT DOCUMENTS						
EXAMINER INITIAL	DOCUMENT NO.	DATE	NAME	CLASS	SUBCLASS	FILING DATE IF APPROPRIATE
	4,916,116	04/10/1990	Yamazaki			
	4,943,558	07/24/1990	Soltis et al.			
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	5,696,392	12/09/1997	Char et al.			
	5,892,243	04/1999	Chan			
	5,904,861	05/1999	Ban et al.			

## FOREIGN PATENT DOCUMENTS

	DOCUMENT NO.	DATE	COUNTRY	CLASS	SUBCLASS	TRANSLATION	
						YES	NO
	0 521 765 A2	01/07/1993	EP				

## OTHER DOCUMENTS (Including Author, Title, Date, Pertinent Pages, Etc.)

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	Agostinelli, J. et al., "Cubic Phase in the Y-Ba-Cu-O System", <i>Physical Review B</i> , Vol. 43, No. 13, pp. 11 396-11 399 (May 1991)
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EXAMINER	DATE CONSIDERED

EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609; draw line through citation if not in conformance and not considered. Include copy of this form for next communication to the Applicant.

<b>FORM 1449*</b> <b>INFORMATION DISCLOSURE STATEMENT</b> <b>IN AN APPLICATION</b> (Use several sheets if necessary)		Docket Number: 10467.43USI2	Application Number: 10/751,091
		Applicant: MOECKLY ET AL.	
		Filing Date: 01/02/2004	Group Art Unit: 1754

	Hunt, B. et al., "High Temperature Superconductor Josephson Weak Links", <i>Second Symposium on Low Temperature Electronics and High Temperature Superconductivity, Electrochemical Society Meeting, Honolulu, Hawaii</i> , Vol. 93-22, pp. 467-472 (May 1993).
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Sheet 3 of 3

<b>FORM 1449*</b> <b>INFORMATION DISCLOSURE STATEMENT</b> <b>IN AN APPLICATION</b> (Use several sheets if necessary)		Docket Number: 10467.43US12	Application Number: 10/751,091
		Applicant: MOECKLY ET AL.	
		Filing Date: 01/02/2004	Group Art Unit: 1754

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**23552**

PATENT TRADEMARK OFFICE

EXAMINER	DATE CONSIDERED
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